

RQK0609CQDQS

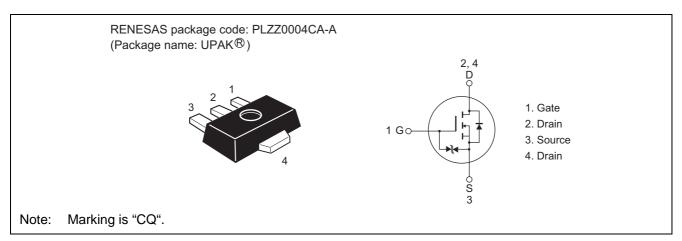
Silicon N Channel MOS FET Power Switching

REJ03G1622-0100 Rev.1.00 Mar 03, 2008

Features

- Low on-resistance
 - $R_{DS(on)} = 78 \text{ m}\Omega \text{ typ.} (\text{at } V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A})$
- Low drive current
- High speed switching
- V_{DSS}: 60 V and capable of 2.5 V gate drive

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

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Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±12	V
Drain current	I _D	4	А
Drain peak current	I _{D(pulse)} Note1	12	А
Body - drain diode reverse drain current	I _{DR}	4	А
Channel dissipation	Pch Note2	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \mu s$, Duty cycle $\le 1\%$

2. When using the glass epoxy board (FR-4 $40\times40\times1$ mm)

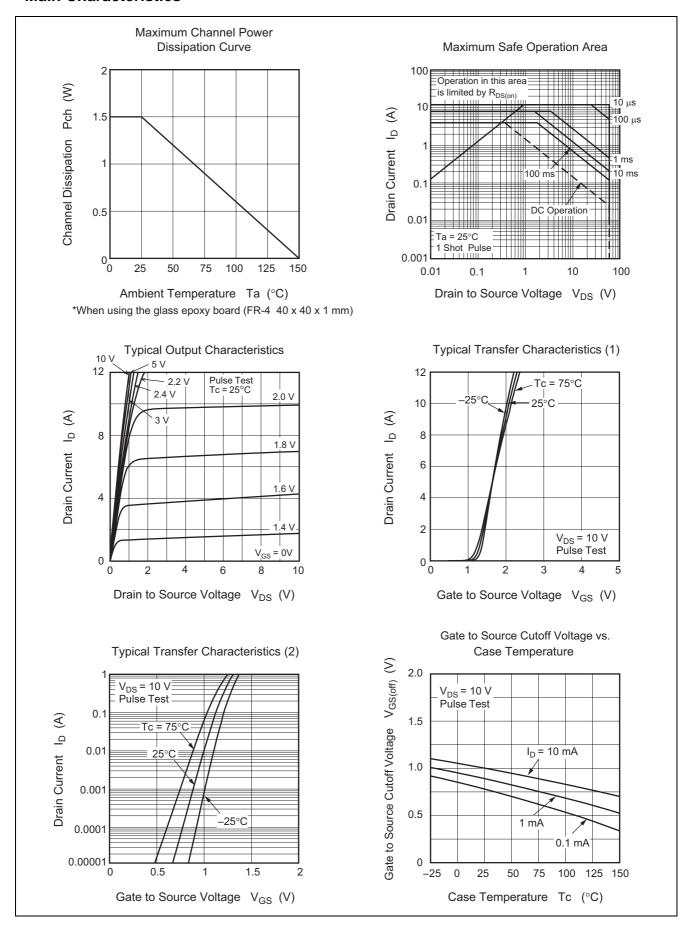
Electrical Characteristics

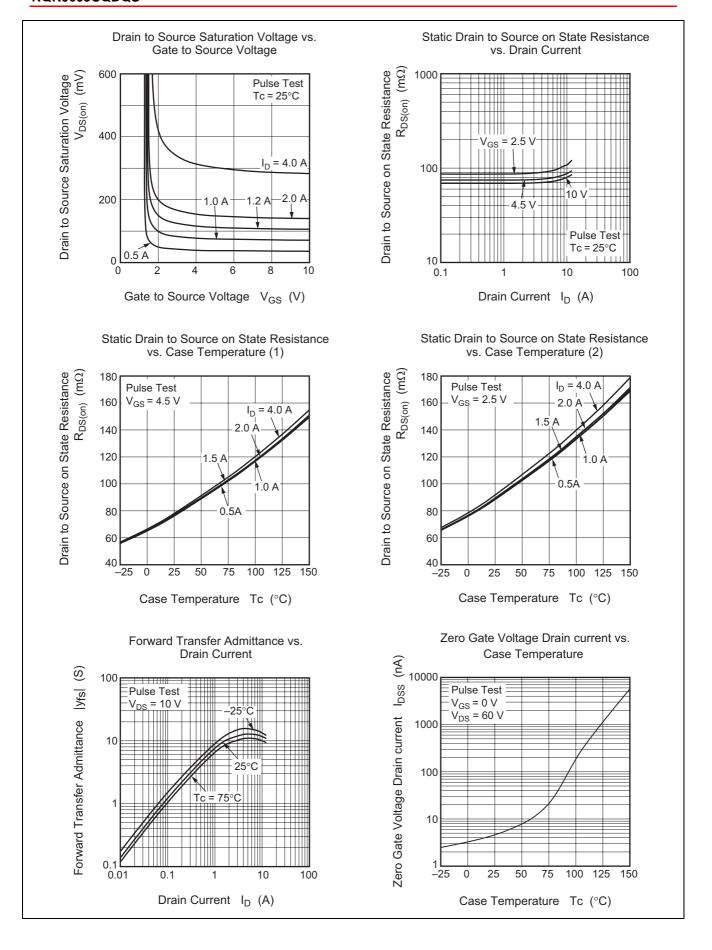
 $(Ta = 25^{\circ}C)$

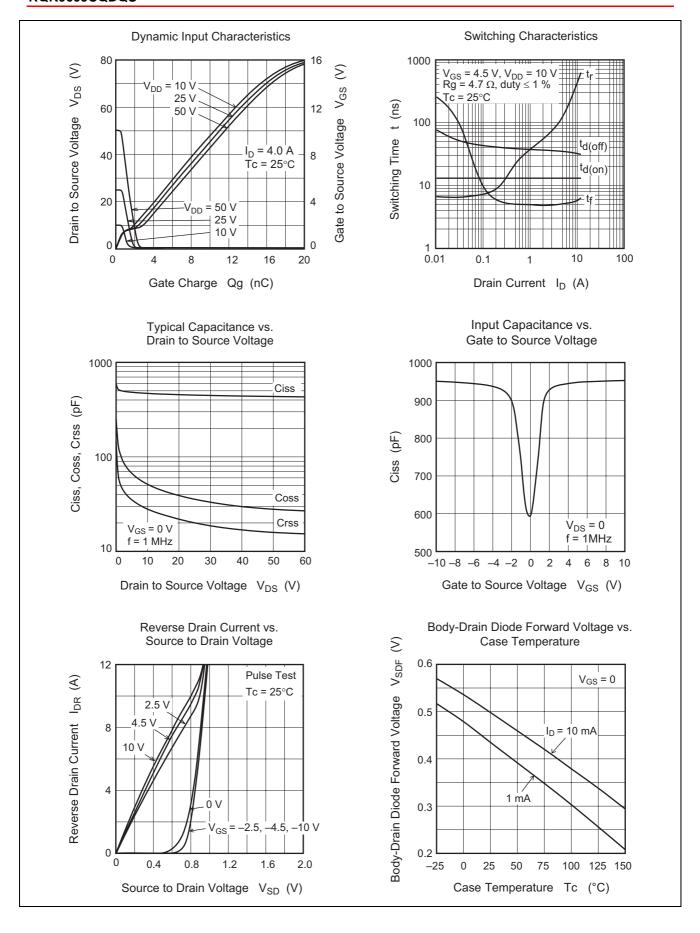
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	+12	_	_	V	$I_G = +100 \mu A, V_{DS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	-12	_	_	V	$I_G = -100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	+10	μΑ	$V_{GS} = +10 \text{ V}, V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	-10	μΑ	$V_{GS} = -10 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.4	_	1.4	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Drain to source on state resistance	R _{DS(on)}	_	78	100	mΩ	$I_D = 2 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note3}}$
Drain to source on state resistance	R _{DS(on)}	_	90	125	mΩ	$I_D = 2 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y _{fs}	7.5	12	_	S	$I_D = 2 A, V_{DS} = 10 V^{Note3}$
Input capacitance	Ciss	_	470	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	52	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	30	_	pF	f = 1 MHz
Turn - on delay time	t _{d(on)}	_	14	_	ns	I _D = 2 A
Rise time	t _r	_	56	_	ns	$V_{GS} = 4.5 \text{ V}$
Turn - off delay time	t _{d(off)}	_	38	_	ns	$R_L = 5 \Omega$
Fall time	t _f	_	5	_	ns	$Rg = 4.7 \Omega$
Total gate charge	Qg	_	5	_	nC	V _{DD} = 10 V
Gate to Source charge	Qgs	_	0.8	_	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Qgd	_	1	_	nC	$I_D = 4 A$
Body - drain diode forward voltage	V_{DF}	_	0.8	_	V	$I_F = 4 \text{ A}, V_{GS} = 0^{\text{Note3}}$

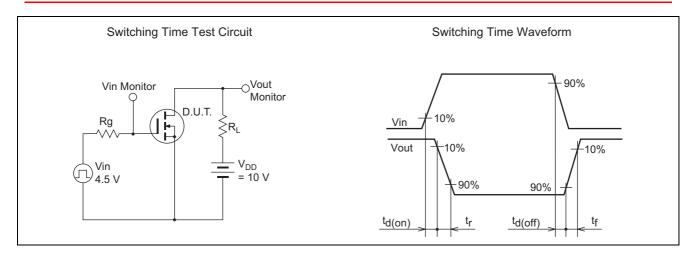
Notes: 3. Pulse test

Main Characteristics

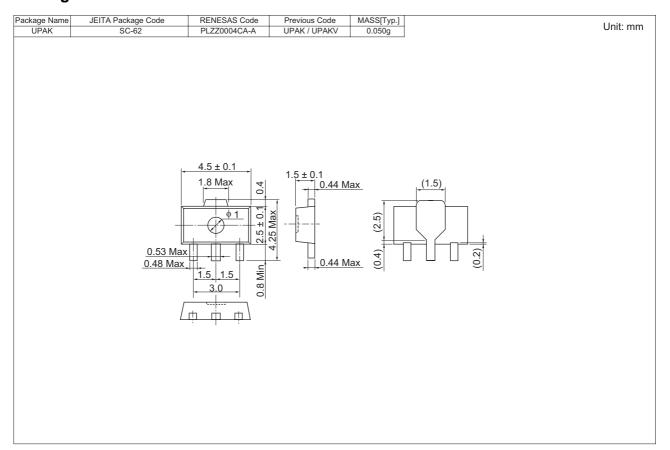








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RQK0609CQDQSTL-E	1000 pcs.	φ178 mm reel, 12 mm Emboss taping

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